

- L1: (1) 10/666649
- L3: (33) (mask\$ near5 (wafer substrate workpiece)) with ((separa\$4) with (rota\$6))
- L4: (80) (mask\$3 near5 (wafer substrate workpiece)) with ((separa\$4 remov\$5 divid\$5) with (rota\$6))
- L5: (8) semiconductor with (mask\$3 near5 (wafer substrate workpiece)) with ((separa\$4 remov\$5 d...)
- L6: (26875) (semiconductor near4 (wafer substrate workpiece)) with (mask\$3 photoresist resist)
- L7: (2217) 6 and ((semiconductor near4 (wafer substrate workpiece)) with (rota\$4 spin\$4))
- L8: (1065) 7 and ((semiconductor near4 (wafer substrate workpiece)) with (separa\$4 remov\$5 div...)
- L9: (479) 8 and ((mask\$3 photoresist resist) with (rota\$4 spin\$4))
- L11: (8) 10 and (wedge)
- L10: (450) 9 and (separa\$ near3 device)
- L12: (467) 9 and (separa\$ near3 device)
- L13: (273) 12 and rota\$4
- L14: (17) 9 and (separa\$ near device)
- L15: (22) 9 and (separa\$ near device wedge adj shap\$3)

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1	<input type="checkbox"/>	<input type="checkbox"/>	US 66491694	20031002	8	Epitaxially coated	428/141	257/E21.23		Wenski, Guido et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
2	<input type="checkbox"/>	<input type="checkbox"/>	US 66491694	20030306	12	Semiconductor wafer with	438/626			Wenski, Guido et al.	<input type="checkbox"/>	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
3	<input type="checkbox"/>	<input type="checkbox"/>	US 66491694	20011206	11	Process for the double-side	216/2	206/712		Wenski, Guido et al.	<input type="checkbox"/>	<input type="checkbox"/>	<input checked="" type="checkbox"/>	<input type="checkbox"/>				
4	<input type="checkbox"/>	<input type="checkbox"/>	US 66491694	20011108	12	Method for converting a	438/471	257/E21.214		Wenski, Guido	<input type="checkbox"/>	<input type="checkbox"/>	<input checked="" type="checkbox"/>	<input type="checkbox"/>				
5	<input type="checkbox"/>	<input type="checkbox"/>	US 66491694	20011101	6	Process for producing a	451/41	257/E21.23		Fabry, Laszlo et al.	<input type="checkbox"/>	<input type="checkbox"/>	<input checked="" type="checkbox"/>	<input type="checkbox"/>				
6	<input type="checkbox"/>	<input type="checkbox"/>	US 66491694	20010816	15	Process for producing a	451/41	257/E21.214		Wenski, Guido et al.	<input type="checkbox"/>	<input type="checkbox"/>	<input checked="" type="checkbox"/>	<input type="checkbox"/>				
7	<input type="checkbox"/>	<input type="checkbox"/>	US 6732689	20040622	13	Apparatus for optical	451/6	156/345.13		Finarov, Moshe	<input type="checkbox"/>	<input type="checkbox"/>	<input checked="" type="checkbox"/>	<input type="checkbox"/>				
8	<input type="checkbox"/>	<input type="checkbox"/>	US 6739944	20040525	25	System for real-time control	451/5	451/10		Sandhu, Gurtej S. et al.	<input type="checkbox"/>	<input type="checkbox"/>	<input checked="" type="checkbox"/>	<input type="checkbox"/>				
9	<input type="checkbox"/>	<input type="checkbox"/>	US 6700091	20040723	21	Method and apparatus for	419/602	257/E21.229		Grobbe, Alvin et al.	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>

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- ✓ L16: (61) "3691694"

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U	Document ID	Issue Date	Pages	Title	Current CR	Current XC	Retrieval C	Inventor	S	C	P	U	V	W
10	✓ US 6756611	20040629	37	Nitride semiconductor growth	257/103	257/13		Kiyoku, Hiroyuki et al.	✓	✓	✓	✓	✓	✓
11	✓ US 6633081	20031014	14	Semiconductor device on a	257/738	257/777		Sahara, Ryutti et al.	✓	✓	✓	✓	✓	✓
12	✓ US 6497784	20021224	10	Semiconductor wafer edge	156/345.12	257/E21.244		Jones, Bradley P. et al.	✓	✓	✓	✓	✓	✓
13	✓ US 6251250	20010626	17	Method of and apparatus for	205/89	204/224R		Keigler, Arthur	✓	✓	✓	✓	✓	✓
14	✓ US 6176967	20010123	5	Reactive ion etch chamber	156/345.3			Obszarny, Christopher	✓	✓	✓	✓	✓	✓
15	✓ US 6153010 A	20001128	35	Method of growing nitride	117/95	117/106		Kiyoku, Hiroyuki et al.	✓	✓	✓	✓	✓	✓
16	✓ US 6117778 A	20000912	10	Semiconductor wafer edge	438/692	257/E21.244		Jones, Bradley P. et al.	✓	✓	✓	✓	✓	✓
17	✓ US 5874329 A	19990223	11	Method for	438/203	257/E21.345		Neary, Paul et al.	✓	✓	✓	✓	✓	✓
18	✓ US 5858112 A	19990112	16	Method for cleaning	134/6	134/32		Yonemizu, Akira et al.	✓	✓	✓	✓	✓	✓
19	✓ US 5830799 A	19981103	24	Method for forming	438/401	148/DIG.102		Ammo, Hiroaki et al.	✓	✓	✓	✓	✓	✓
20	✓ US 5651160 A	19970729	16	Cleaning apparatus for	15/302	134/902		Yonemizu, Akira et al.	✓	✓	✓	✓	✓	✓
21	✓ US 5491109 A	19960213	15	Method for the construction	438/624	257/E21.576		Kim, Jae G.	✓	✓	✓	✓	✓	✓
22	✓ US 4876216 A	19891024	7	Semiconductor integrated	438/437	257/E21.548		Tobias, Eric et al.	✓	✓	✓	✓	✓	✓

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U	Document ID	Issue Date	Pages	Title	Current CR	Current X12	Retireval	Inventor	S	C	I	Y	Z
1	US 20041021	60		Pattern forming method and	430/311	427/255.23;		Mori, Yoshiaki et al.	✓	✓	✓	✓	✓
2	US 20040624	10		Angled wafer rotating ion	438/302			Wang, Tzu-Yu	✓	✓	✓	✓	✓
3	US 20040520	38		Nitride semiconductor growth	257/103	257/627;		Kiyoku, Hiroyuki et al.	✓	✓	✓	✓	✓
4	US 20040325	8		Computer controlled	438/540			Molina, Michael	✓	✓	✓	✓	✓
5	US 20040304	97		Processing method	430/22	250/396R;		Takeishi, Tomoyuki et	✓	✓	✓	✓	✓
6	US 20030306	34		Method for developing	430/325	396/611;		Yoshihara, Kousuke et	✓	✓	✓	✓	✓
7	US 20030227	37		Nitride semiconductor growth	117/84	257/E21.108;		Kiyoku, Hiroyuki et al.	✓	✓	✓	✓	✓
8	US 20021205	16		Semiconductor device and	257/738	257/E23.178		Sahara, Ryutti et al.	✓	✓	✓	✓	✓
9	US 20020425	42		Nitride semiconductor growth	117/8	257/E21.108;		Kiyoku, Hiroyuki et al.	✓	✓	✓	✓	✓
10	US 6756611	20040629	37	Nitride semiconductor growth	257/103	257/13;		Kiyoku, Hiroyuki et al.	✓	✓	✓	✓	✓
11	US 6633081	20031014	14	Semiconductor device on a	257/738	257/777;		Sahara, Ryutti et al.	✓	✓	✓	✓	✓
12	US 6497784	20021224	10	Semiconductor wafer edge	156/345.12	257/E21.244		Jones, Bradley P. et al.	✓	✓	✓	✓	✓
13	US 6251250	20010626	17	Method of and apparatus for	205/89	204/224R;		Keigler, Arthur	✓	✓	✓	✓	✓
14	US 6176967	20010123	5	Reactive ion etch chamber	156/345.3			Obszarny, Christopher	✓	✓	✓	✓	✓